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Publication Lists

A. International Letter:

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B. International Journal:

[1] **Ting-Kuo Chang**, Ching-Wei Lin, Yuan-Hsun Chang, Chang-Ho Tesng, Fang-Tsun Chu, Li-Jen Chou, and Hunag-Chung Cheng "Thickness dependence of microstructure of laterally crystallized poly-Si thin film and electrical characteristics of low-temperature poly-Si TFTs," ***J. Electrochem. Soc.*** vol. 150, pp. G494-497, 2003.

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